

16. (New) The method according to claim 15, further comprising the step of removing the nitride layer at least in subareas of the positive areas after the negative areas are provided with the first passivation layer and before the wafer is etched.

17. (New) The method according to claim 15, wherein the structuring step includes a step of removing a photoresist at at least one of the edge areas after exposing the photoresist.

18. (New) The method according to claim 17, wherein the photoresist is removed after exposing and developing the photoresist.

19. (New) The method according to claim 18, further comprising the step of applying the oxide layer in a LOCOS process.

20. (New) The method according to claim 14, wherein the passivation layer includes an oxide layer.

21. (New) The method according to claim 14, wherein the step of etching the wafer in the wet chemical etching process is performed so that at least one through hole is etched out.

22. (New) The method according to claim 14, wherein the step of etching the wafer in the wet chemical etching process is performed so that a cavern area is formed in the vicinity of the at least one positive area provided with the second passivation layer.

23. (New) The method according to claim 22, wherein the step of etching the wafer in the wet chemical etching process is performed so that at least one through hole is etched out.

24. (New) The method according to claim 14, wherein the wafer is made of a single material.